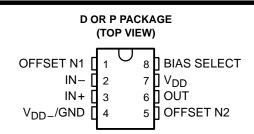
TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS SLOS001F – JULY 1983 – REVISED MARCH 2001

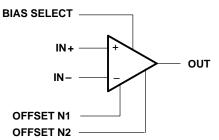
- Wide Range of Supply Voltages 1.4-V to 16-V
- True Single-Supply Operation
- Common-Mode Input Voltage Range Includes the Negative Rail
- Low Noise ... 30 nV/√Hz Typ at 1-kHz (High Bias)
- ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015.1

description

The TLC251C, TLC251AC, and TLC251BC are low-cost, low-power programmable operational amplifiers designed to operate with single or dual supplies. Unlike traditional metal-gate CMOS operational amplifiers, these devices utilize Texas Instruments silicon-gate LinCMOS[™] process, giving them stable input offset voltages without sacrificing the advantages of metal-gate CMOS.



symbol



This series of parts is available in selected grades of input offset voltage and can be nulled with one external potentiometer. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this family is ideally suited for battery-powered or energy-conserving applications. A bias-select pin can be used to program one of three ac performance and power-dissipation levels to suit the application. The series features operation down to a 1.4-V supply and is stable at unity gain.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in a degradation of the device parametric performance.

Because of the extremely high input impedance and low input bias and offset currents, applications for the TLC251C series include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOS[™] operational amplifiers without the power penalties of traditional bipolar devices. Remote and inaccessible equipment applications are possible using the low-voltage and low-power capabilities of the TLC251C series.

In addition, by driving the bias-select input with a logic signal from a microprocessor, these operational amplifiers can have software-controlled performance and power consumption. The TLC251C series is well suited to solve the difficult problems associated with single battery and solar cell-powered applications.

The TLC251C series is characterized for operation from 0°C to 70°C.

-	_			
	Viemov	PACKAGEI	DEVICES	CHIP FORM
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	PLASTIC DIP (P)	(Y)
0°C to 70°C	10 mV 5 mV 2 mV	TLC251CD TLC251ACD TLC251BCD	TLC251CP TLC251ACP TLC251BCP	TLC251Y — —

AVAILABLE OPTIONS

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC251CDR). Chips are tested at 25°C.

LinCMOS is a trademark of Texas Instruments.

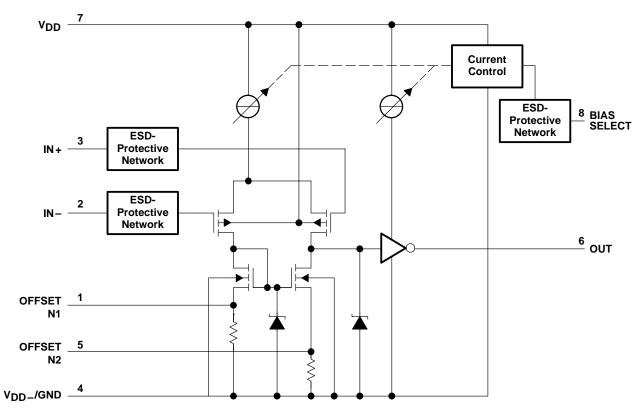
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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schematic

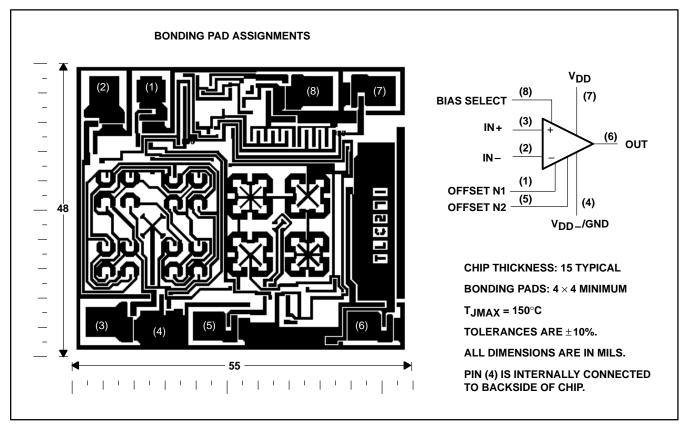




TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS SLOS001F – JULY 1983 – REVISED MARCH 2001

TLC251Y chip information

These chips, properly assembled, display characteristics similar to the TLC251C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1)	18 V
Differential input voltage, VID (see Note 2)	
Input voltage range, V _I (any input)	0.3 V to 18 V
Duration of short circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range	−65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to V_D_/GND.

- 2. Differential voltages are at IN+ with respect to IN-.
- 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

	DISSIPATIC	IN RATING TABLE	
PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V _{DD}		1.4	16	V
	V _{DD} = 1.4 V	0	0.2	
	$V_{DD} = 5 V$	-0.2	4	v
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	9	v
	V _{DD} = 16 V	-0.2	14	
Operating free-air temperature, TA		0	70	°C
Bias-select voltage			e Applica Informati	



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HIGH-BIAS MODE

electrical characteristics at specified free-air temperature

					т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	т _А †	v	DD = 5 \	/	V	OD = 10	v	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		-		25°C		1.1	10		1.1	10	
		TLC251C		Full range			12			12	
			$V_{O} = 1.4 V,$ $V_{IC} = 0 V,$	25°C		0.9	5		0.9	5	
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 kΩ	25°C		0.34	2		0.39	2	
		TLC251BC		Full range			3			3	
αVIO	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.8			2		μV/°C
L -	Innut offect ourrest (a	an Nota ()	$V_{O} = V_{DD}/2,$	25°C		0.1	60		0.1	60	-
IO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	рA
	Innut biog gurrant (og	a Nata ()	$V_{O} = V_{DD}/2,$	25°C		0.6	60		0.7	60	~^
IВ	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	рA
	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)	- enage		Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	3.8		8	8.5		
Vон	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 10 \text{ k}\Omega$	0°C	3	3.8		7.8	8.5		V
			KL = 10 K22	70°C	3	3.8		7.8	8.4		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			10L = 0	70°C		0	50		0	50	
				25°C	5	23		10	36		
AVD	Large-signal different amplification	ial voltage	$R_{L} = 10 \text{ k}\Omega$, See Note 6	0°C	4	27		7.5	42		V/mV
				70°C	4	20		7.5	32		
				25°C	65	80		65	85		
CMRR	Common-mode rejec	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	84		60	88		dB
				70°C	60	85		60	88		
	Supply-voltage reject	ion ratio	V _{DD} = 5 V to 10 V,	25°C	65	95		65	95		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V to 10 V,$ $V_{O} = 1.4 V$	0°C	60	94		60	94		dB
			-	70°C	60	96		60	96		
II(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = 0$	25°C		-1.4			-1.9		μA
			$V_{O} = V_{DD}/2,$	25°C		675	1600		950	2000	
IDD	Supply current		$V_{IC} = V_{DD}/2$, No load	0°C		775	1800		1125	2200	μA
			ino luau	70°C		575	1300		750	1700	

[†]Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 V$, $V_{O} = 0.25 V$ to 2 V; at $V_{DD} = 10 V$, $V_{O} = 1 V$ to 6 V.



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HIGH-BIAS MODE

operating characteristics, V_{DD} = 5 V

	PARAMETER	т	EST CONDITIO	ONS	Тд	TLC2510 TL	C, TLC2 C251BC		UNIT
						MIN	TYP	MAX	
					25°C		3.6		
				V _{I(PP)} = 1 V	0°C		4		
SR	Slow rate at unity gain	R _L = 10 kΩ,	$C_{1} = 20 \text{ pF}$		70°C		3		\//uo
SK	Slew rate at unity gain	KL = 10 Ksz,	CL = 20 pr		25°C		2.9		V/μs
				VI(PP) = 2.5 V	0°C		3.1		
					70°C		2.5		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		25		nV/√Hz
					25°C		320		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 10 \ k\Omega$	0°C		340		kHz
					70°C		260		
					25°C		1.7		
B ₁	Unity-gain bandwidth	Vj = 10 mV,	C _L = 20 pF		0°C		2		MHz
					70°C		1.3		
					25°C		46°		
[¢] m	Phase margin	Vj = 10 mV,	f = B ₁ ,	C _L = 20 pF	0°C		47°		
					70°C		44°		

operating characteristics, V_{DD} = 10 V

	PARAMETER	1		ONS	ТА	TLC251 TL	C, TLC2 .C251B(UNIT
						MIN	TYP	MAX	
					25°C		5.3		
				VI(PP) = 1 V	0°C		5.9		
SR	Slew rate at unity gain	$P_{\rm L} = 10 \rm kO$	$C_{1} = 20 \text{ pE}$		70°C		4.3		\//uo
SK	Siew rate at unity gain	$R_L = 10 k\Omega$,	CL = 20 pr		25°C		4.6		V/μs
				V _{I(PP)} = 5.5 V	0°C		5.1		
					70°C		3.8		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		25		nV/√Hz
					25°C		200		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 10 \ k\Omega$	0°C		220		kHz
					70°C		140		
					25°C		2.2		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	$C_L = 20 \text{ pF}$		0°C		2.5		MHz
					70°C		1.8		
					25°C		49°		
фт	Phase margin	V _I = 10 mV,	$f = B_1,$	C _L = 20 pF	0°C		50°		
					70°C		46°		



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MEDIUM-BIAS MODE

electrical characteristics at specified free-air temperature

					т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		UNIT					
			CONDITIONS					MIN	TYP	MAX	
		-		25°C		1.1	10		1.1	10	
		TLC251C		Full range			12			12	
.,		_	$V_{O} = 1.4 V,$ $V_{IC} = 0 V,$	25°C		0.9	5		0.9	5	.,
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 kΩ	25°C		0.34	2		0.39	2	
		TLC251BC		Full range			3			3	
αΛΙΟ	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.7			2.1		μV/°C
	lanut offent summert (s	an Nata ()	$V_{O} = V_{DD}/2,$	25°C		0.1	60		0.1	60	- 4
IO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	pА
lun.	Input biog ourropt (og	a Nata ()	$V_{O} = V_{DD}/2,$	25°C		0.6	60		0.7	60	n A
lΒ	Input bias current (se	e Nole 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	pА
.,	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)			Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	3.9		8	8.7		
Vон	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 10 \text{ k}\Omega$	0°C	3	3.9		7.8	8.7		V
				70°C	3	4		7.8	8.7		
			100 V	25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			IOL - 0	70°C		0	50		0	50	
	1		D (0)0	25°C	25	170		25	275		
AVD	Large-signal different amplification	lai voltage	$R_L = 10 k\Omega$, See Note 6	0°C	15	200		15	320		V/mV
				70°C	15	140		15	230		
				25°C	65	91		65	94		
CMRR	Common-mode rejec	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	91		60	94		dB
				70°C	60	92		60	94		
	Supply-voltage reject	ion ratio	V _{DD} = 5 V to 10 V,	25°C	70	93		70	93		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{\rm DD} = 5 V 10 10 V,$ $V_{\rm O} = 1.4 V$	0°C	60	92		60	92		dB
	-			70°C	60	94		60	94		
II(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = V_{DD}/2$	25°C		-130			-160		nA
			$V_{O} = V_{DD}/2$,	25°C		105	280		143	300	_
IDD	Supply current		V _{IC} = V _{DD} /2, No load	0°C		125	320		173	400	μA
				70°C		85	220		110	280	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 V$, $V_{O} = 0.25 V$ to 2 V; at $V_{DD} = 10 V$, $V_{O} = 1 V$ to 6 V.



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MEDIUM-BIAS MODE

operating characteristics, $V_{DD} = 5 V$

	PARAMETER	т	EST CONDITIC	DNS	TA	TLC251 TL	C, TLC2 .C251B(UNIT
						MIN	TYP	MAX	
					25°C		0.43		
				V _{I(PP)} = 1 V	0°C		0.46		
SR	Slew rate at unity gain	R _L = 100 kΩ,	$C_{1} = 20 \text{ pE}$		70°C		0.36		\//uo
SK	Siew rate at unity gain	$K_{L} = 100 \text{ ks}_{2}$	CL = 20 pr		25°C		0.40		V/μs
				VI(PP) = 2.5 V	0°C		0.43		
					70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		32		nV/√Hz
					25°C		55		
BOM	Maximum output-swing bandwidth	$V_{O} = V_{OH},$	C _L = 20 pF,	$R_L = 100 \text{ k}\Omega$	0°C		60		kHz
					70°C		50		
					25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	CL = 20 pF		0°C		600		kHz
					70°C		400		
					25°C		40°		
φm	Phase margin	V _I = 10 mV,	f = B ₁ ,	C _L = 20 pF	0°C		41°		
					70°C		39°		

operating characteristics, V_{DD} = 10 V

	PARAMETER	т	EST CONDITIC	ONS	ТА	TLC251 TL	C, TLC2 .C251B(UNIT
						MIN	TYP	MAX	
					25°C		0.62		
				VI(PP) = 1 V	0°C		0.67		
SR	Slow rate at unity gain	$P_{\rm L} = 100 \rm kg$	$C_{\rm L} = 20 \rm pE$		70°C		0.51)//uo
SK	Slew rate at unity gain	R _L = 100 kΩ,	CL = 20 pr		25°C		0.56		V/μs
				VI(PP) = 5.5 V	0°C		0.61		
					70°C		0.46		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		32		nV/√Hz
					25°C		35		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 100 \text{ k}\Omega$	0°C		40		kHz
					70°C		30		
					25°C		635		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	CL = 20 pF		0°C		710		kHz
					70°C		510		
					25°C		43°		
[¢] m	Phase margin	V _I = 10 mV,	f = B ₁ ,	C _L = 20 pF	0°C		44°		
					70°C		42°		



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LOW-BIAS MODE

electrical characteristics at specified free-air temperature

					т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	тд†	v	DD = 5 \	/	V	88		UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		-		25°C		1.1	10		1.1	10	
		TLC251C		Full range			12			12	
.,		_	V _O = 1.4 V, V _{IC} = 0 V,	25°C		0.9	5		0.9	5	.,
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 MΩ	25°C		0.24	2		0.26	2	
		TLC251BC		Full range			3			3	
αVIO	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.1			1		μV/°C
L =	Innut offect ourrest (a	an Nota ()	$V_{O} = V_{DD}/2,$	25°C		0.1	60		0.1	60	~^
IO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	рA
	Innut biog gurrant (og	o Noto ()	$V_{O} = V_{DD}/2,$	25°C		0.6	60		0.7	60	~^
IВ	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	рA
	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)	- enage		Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	4.1		8	8.9		
∨он	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 1 \text{ M}\Omega$	0°C	3	4.1		7.8	8.9		V
				70°C	3	4.2		7.8	8.9		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			10L - 0	70°C		0	50		0	50	
			5 (11)	25°C	50	520		50	870		
AVD	Large-signal different amplification	ial voltage	$R_L = 1 M\Omega$, See Note 6	0°C	50	700		50	1030		V/mV
				70°C	50	380		50	660		
				25°C	65	94		65	97		
CMRR	Common-mode rejec	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	95		60	97		dB
				70°C	60	95		60	97		
	Supply-voltage reject	ion ratio	V _{DD} = 5 V to 10 V,	25°C	70	97		70	97		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{\rm O} = 3.4 \rm V$	0°C	60	97		60	97		dB
			-	70°C	60	98		60	98		
II(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = V_{DD}$	25°C		65			95		nA
			$V_{O} = V_{DD}/2,$	25°C		10	17		14	23	
IDD	Supply current		V _{IC} = V _{DD} /2, No load	0°C		12	21		18	33	μA
				70°C		8	14		11	20	

[†]Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 V$, $V_{O} = 0.25 V$ to 2 V; at $V_{DD} = 10 V$, $V_{O} = 1 V$ to 6 V.



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LOW-BIAS MODE

operating characteristics, $V_{DD} = 5 V$

	PARAMETER	1	EST CONDITIC	ONS	Тд	TLC251 TL	C, TLC2 .C251B(UNIT
						MIN	TYP	MAX	
					25°C		0.03		
				VI(PP) = 1 V	0°C		0.04		
SR	Slew rate at unity gain	R _L = 1 MΩ,	CL = 20 pF		70°C		0.03		V/µs
SK	Siew rate at unity gain	$K_{L} = 1 \text{ IVIS2},$	0L = 20 pr		25°C		0.03		v/µs
				V _{I(PP)} = 2.5 V	0°C		0.03		
					70°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		68		nV/√Hz
					25°C		5		
BOM	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 1 M\Omega$	0°C		6		kHz
					70°C		4.5		
					25°C		85		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		0°C		100		kHz
					70°C		65		
					25°C		34°		
φm	Phase margin	Vj = 10 mV,	f = B ₁ ,	CL = 20 pF	0°C		36°		
					70°C		30°		

operating characteristics, V_{DD} = 10 V

	PARAMETER	г		ONS	ТА		TLC251C, TLC251AC, TLC251BC		
						MIN	TYP	MAX	
					25°C		0.05		
				V _{I(PP)} = 1 V	0°C		0.05		
SR	Slow rate at unity gain	$\mathbf{P}_{1} = 1 \mathbf{M}_{0}$	$C_{1} = 20 \text{ pF}$		70°C		0.04		\//uo
SK	Slew rate at unity gain	$R_{L} = 1 M\Omega$,	CL = 20 pF		25°C		0.04		V/μs
				VI(PP) = 5.5 V	0°C		0.05		
				, ,	70°C		0.04		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω	-	25°C		68		nV/√Hz
					25°C		1		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 1 M\Omega$	0°C		1.3		kHz
					70°C		0.9		
					25°C		110		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		0°C		125		kHz
					70°C		90		
					25°C		38°		
[¢] m	Phase margin	V _I = 10 mV,	f = B ₁ ,	C _L = 20 pF	0°C		40°		
					70°C		34°		



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	PARAMETE	R	TEST COND	ITIONS [†]	т _А ‡	BIAS	TLC251 TL	C, TLC2 .C251BC		UNIT
	T- 00540						MIN	TYP	MAX	
		TLC251C			25°C	Any			10	
		1202510			Full range	Any			12	
VIO	Input offset	TLC251AC	V _O = 0.2 V,	R _S = 50 Ω	25°C	Any			5	mV
VIO	voltage	TLOZSTAC	VO = 0.2 V,	NS = 30.22	Full range	Any			6.5	IIIV
		TLC251BC			25°C	Any			2	
		TLOZSTBC			Full range	Any			3	
αΛΙΟ	Average temp coefficient of i voltage				25°C to 70°C	Any		1		μV/°C
li o	Input offset cu	rroot	V _O = 0.2 V		25°C	Any		1	60	pА
IIO	input onset ct	literit	VO = 0.2 V		Full range	Any			300	рА
lin	Input bias cur	rent	V _O = 0.2 V		25°C	Any		1	60	pА
IВ	input bias cui	Terit	V() = 0.2 V		Full range	Any			600	рА
VICR	Common-moo voltage range				25°C	Any	0 to 0.2			V
V _{OM}	Peak output v swing§	roltage	V _{ID} = 100 mV		25°C	Any	450	700		mV
A. (5)	Large-signal	differential	$V_{O} = 100 \text{ to } 300 \text{ mV},$	$P_{0} = 50.0$	25°C	Low		20		
AVD	voltage ampli	fication	$v_0 = 100 to 300 mV,$	NS = 50 22	25 0	High		10		
CMRR	Common-moo ratio	de rejection	$R_S = 50 \Omega$, V _{IC} = V _{ICR} min	V _O = 0.2 V,	25°C	Any	60	77		dB
100	Supply currer	,+	V _O = 0.2 V,	No load	25°C	Low		5	17	μA
IDD	Supply culler	n.	v U = 0.2 v,	NU IUau	25 0	High		150	190	μΑ

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following values: for low bias, R_L = 1 MΩ, for medium bias,

, $R_L = 100 \text{ k}\Omega$, and for high bias, $R_L = 10 \text{ k}\Omega$.

[‡]Full range is 0°C to 70°C.

 $\$ The output swings to the potential of V_DD_/GND.

operating characteristics, V_{DD} = 1.4 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT
				MIN	TYP	MAX	
р.	Unity-gain bandwidth	$C_{1} = 100 \text{ pE}$	Low		12		kHz
В ₁	Onity-gain bandwidth	C _L = 100 pF	High	12			NI IZ
SR	Slew rate at unity gain	See Figure 1	Low	0.001)//uo
SK	Siew fate at unity gain	See Figure 1	High		0.1		V/µs
	Overshoot factor	See Figure 1	Low		35%		
		See Figure 1	High		30%		



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electrical characteristics, $V_{DD} = 5 V$, $T_A = 25^{\circ}C$

						٦	LC251	(
	PARAMETER	TEST CONDITIONS		GH-BIA MODE	S		DIUM-B MODE	IAS	L	OW-BIA MODE	S	UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
VIO	Input offset voltage			1.1	10		1.1	10		1.1	10	mV
αΛΙΟ	Average temperature coefficient of input offset voltage			1.8			1.7			1.1		μV/°C
IIO	Input offset current (see Note 4)	$V_{O} = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.1	60		0.1	60		0.1	60	pА
I _{IB}	Input bias current (see Note 4)	$V_{O} = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.6	60		0.6	60		0.6	60	pА
VICR	Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		V
VOH	High-level output voltage	V _{ID} = 100 mV, RL [†]	3.2	3.8		3.2	3.9		3.2	4.1		V
V _{OL}	Low-level output voltage	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$		0	50		0	50		0	50	mV
AVD	Large-signal differential voltage amplification	V _O = 0.25 V, R _L †	5	23		25	170		50	480		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$	65	80		65	91		65	94		dB
^k SVR	Supply-voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	V _{DD} = 5 V to 10 V, V _O = 1.4 V	65	95		70	93		70	97		dB
II(SEL)	Input current (BIAS SELECT)	$V_{I(SEL)} = V_{DD}/2$		-1.4			-0.13			0.065		μΑ
IDD	Supply current	$V_{O} = V_{DD}/2,$ $V_{IC} = V_{DD}/2,$ No load		675	1600		105	280		10	17	μA

[†] For high-bias mode, R_L = 10 k Ω ; for medium-bias mode, R_L = 100 k Ω ; and for low-bias mode, R_L = 1 M Ω .

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



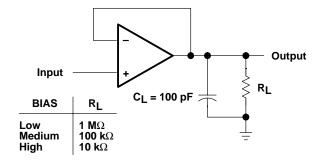
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							Т	LC251	(
	PARAMETER	TEST CONDITIONS		HIGH-BIAS MODE		MEDIUM-BIAS MODE			LOW-BIAS MODE			UNIT	
				MIN	ТҮР	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at	RL [†] ,	V _{I(PP)} = 1 V		3.6			0.43			0.03		V/µs
3K	unity gain	C_ = 20 pF	V _{I(PP)} = 2.5 V		2.9			0.40			0.03		v/µs
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25			32			68		nV/√Hz
BOM	Maximum output swing bandwidth	$V_{O} = V_{OH},$ R _L = 10 k Ω	C _L = 20 pF,		320			55			4.5		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF	1	1700			525			65		kHz
φm	Phase margin	f = B ₁ , C _L = 20 pF	V _I = 10 mV,		46°			40°			34°		

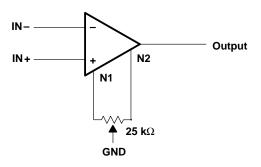
operating characteristics, V_DD = 5 V, T_A = 25°C

[†] For high-bias mode, $R_L = 10 \text{ k}\Omega$; for medium-bias mode, $R_L = 100 \text{ k}\Omega$; and for low-bias mode, $R_L = 1 \text{ M}\Omega$.

PARAMETER MEASUREMENT INFORMATION









TYPICAL CHARACTERISTICS

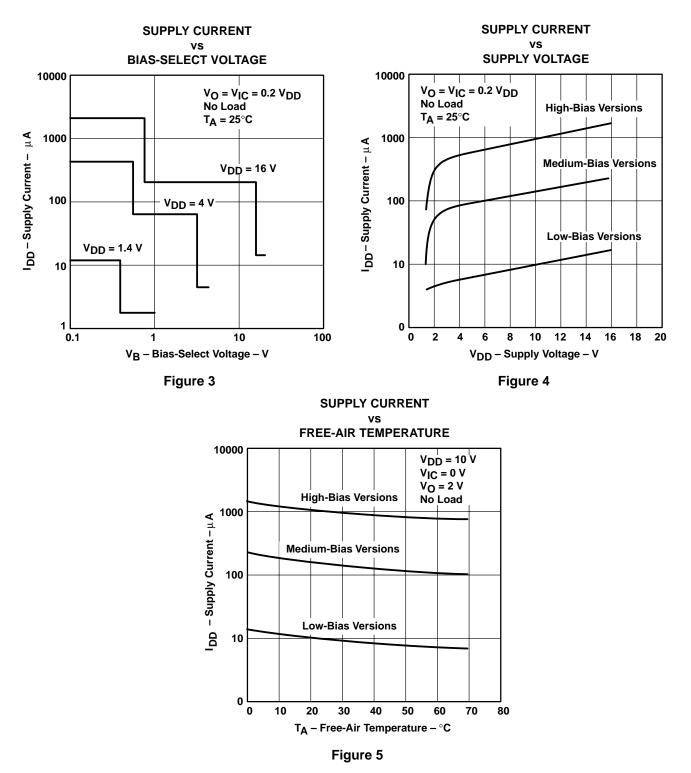
Table of Graphs

				FIGURE
IDD	Supply current		vs Bias-select voltage vs Supply voltage vs Free-air temperature	3 4 5
		Low bias	vs Frequency	6
AVD	Large-signal differential voltage amplification Medium bias vs Frequency		vs Frequency	7
		High bias	vs Frequency	8
		Low bias	vs Frequency	6
	Phase shift	Medium bias	vs Frequency	7
		High bias	vs Frequency	8



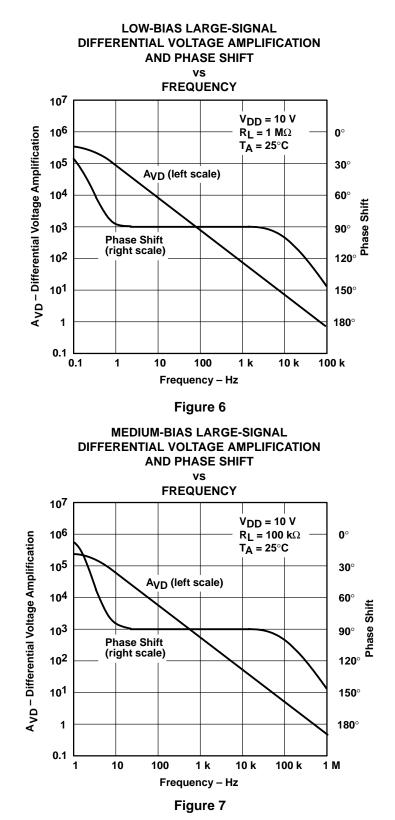
TLC251, TLC251A, TLC251B, TLC251Y LinCMOS[™] PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS SLOS001F – JULY 1983 – REVISED MARCH 2001

TYPICAL CHARACTERISTICS





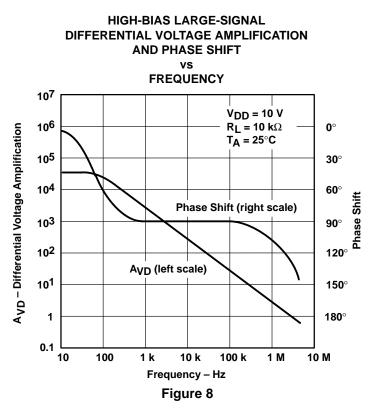
TYPICAL CHARACTERISTICS





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APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNPN structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifier supplies should be applied simultaneously with, or before, application of any input signals.



APPLICATION INFORMATION

using BIAS SELECT

The TLC251 has a terminal called BIAS SELECT that allows the selection of one of three I_{DD} conditions (10, 150, and 1000 μ A typical). This allows the user to trade-off power and ac performance. As shown in the typical supply current (I_{DD}) versus supply voltage (V_{DD}) curves (Figure 4), the I_{DD} varies only slightly from 4 V to 16 V. Below 4 V, the I_{DD} varies more significantly. Note that the I_{DD} values in the medium- and low-bias modes at $V_{DD} = 1.4$ V are typically 2 μ A, and in the high mode are typically 12 μ A. The following table shows the recommended BIAS SELECT connections at $V_{DD} = 10$ V.

BIAS MODE	AC PERFORMANCE	BIAS SELECT CONNECTION [†]	TYPICAL IDD [‡]
Low	Low	V _{DD}	10 µA
Medium	Medium	0.8 V to 9.2 V	150 μA
High	High	Ground pin	1000 μA

Bias selection may also be controlled by external circuitry to conserve power, etc. For information regarding BIAS SELECT, see Figure 3 in the typical characteristics curves.

[‡] For I_{DD} characteristics at voltages other than 10 V, see Figure 4 in the typical characteristics curves.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD} –/GND.

input offset nulling

The TLC251C series offers external offset null control. Nulling may be achieved by adjusting a 25-k Ω potentiometer connected between the offset null terminals with the wiper connected to the device V_{DD}/GND pin as shown in Figure 2. The amount of nulling range varies with the bias selection. At an I_{DD} setting of 1000 μ A (high bias), the nulling range allows the maximum offset specified to be trimmed to zero. In low or medium bias or when the amplifier is used below 4 V, total nulling may not be possible for all units.

supply configurations

Even though the TLC251C series is characterized for single-supply operation, it can be used effectively in a split-supply configuration when the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

The user is cautioned that whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup, as well as excessive dc leakages.



7-May-2007

PACKAGING INFORMATION

MENTS

www ti com

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC251ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251ACPE4	ACTIVE	PDIP	Ρ	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251BCPE4	ACTIVE	PDIP	Ρ	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC251CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC251CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

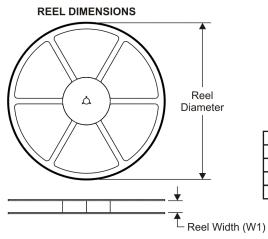


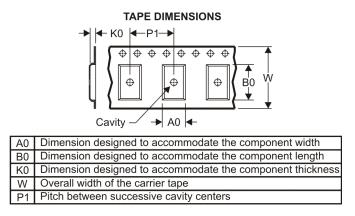
⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

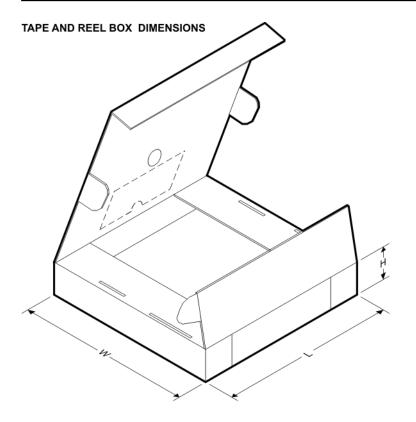


*A	Il dimensions are nominal												
	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	TLC251ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
	TLC251CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
	TLC251CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1



PACKAGE MATERIALS INFORMATION

11-Mar-2008



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC251ACDR	SOIC	D	8	2500	346.0	346.0	29.0
TLC251CDR	SOIC	D	8	2500	346.0	346.0	29.0
TLC251CPSR	SO	PS	8	2000	346.0	346.0	33.0

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